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PBSS5240Z 40 V, 2 A PNP low VCEsat (BISS) transistor 15 October 2014

**Product data sheet** 

#### 1. **General description**

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4240Z

#### Features and benefits 2.

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_C$  and  $I_{CM}$ •
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

#### **Applications** 3.

- DC-to-DC conversion •
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs) •
- Inductive load driver (e.g. relays, buzzers and motors) •

#### Quick reference data 4.

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-40	V
I <sub>C</sub>	collector current		-	-	-2	А
I <sub>CM</sub>	peak collector current	$t_p \le 1 \text{ ms}$ ; single pulse	-	-	-3	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	320	mΩ







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# 5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	4	2,4
2	С	collector		1-1
3	E	emitter		
4	С	collector	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	3 sym028

# 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PBSS5240Z	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223				

## 7. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS5240Z	S5240Z



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### 8. Limiting values

#### Table 5. Limiting values

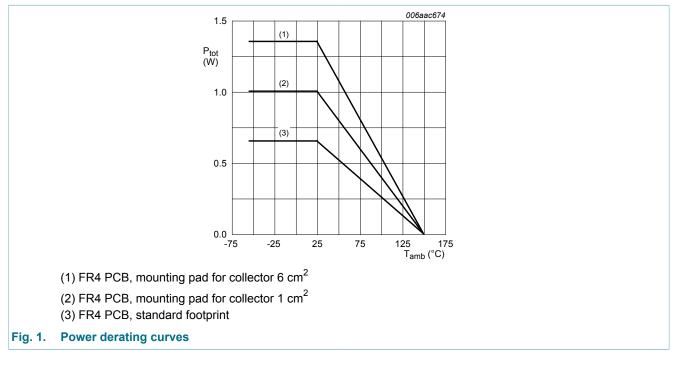
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-40	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-7	V
I <sub>C</sub>	collector current			-	-2	А
I <sub>CM</sub>	peak collector current	$t_p \le 1 \text{ ms}$ ; single pulse		-	-3	А
I <sub>B</sub>	base current			-	-300	mA
I <sub>BM</sub>	peak base current	$t_p \le 1$ ms; single pulse		-	-1	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	0.65	W
			[2]	-	1	W
			[3]	-	1.35	W
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.



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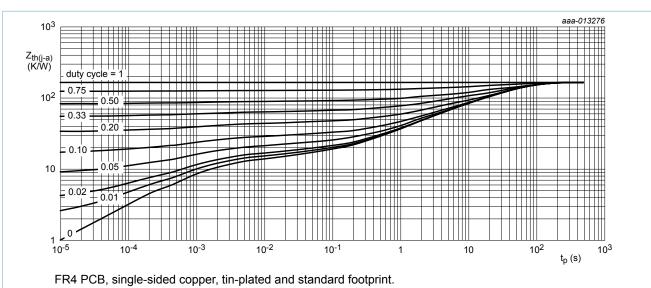
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## 9. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	192	K/W
			[2]	-	-	125	K/W
			[3]	-	-	93	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

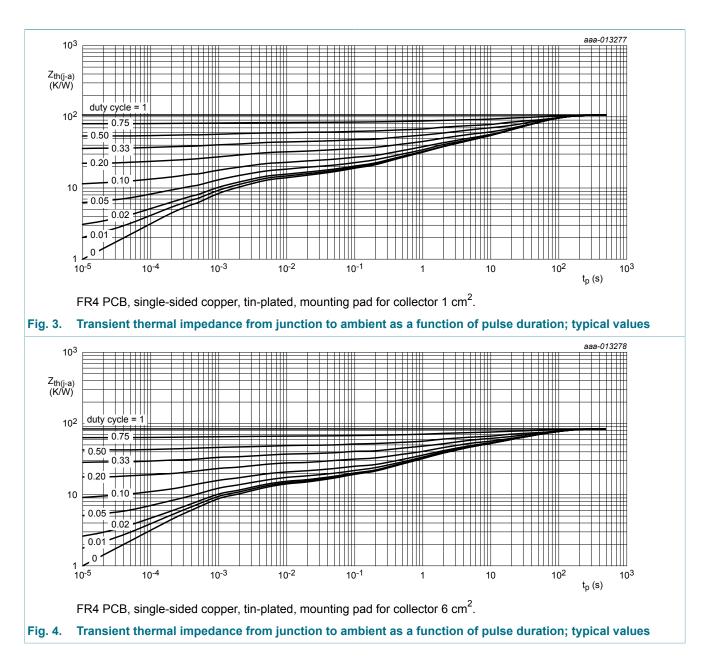


[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



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# **10. Characteristics**

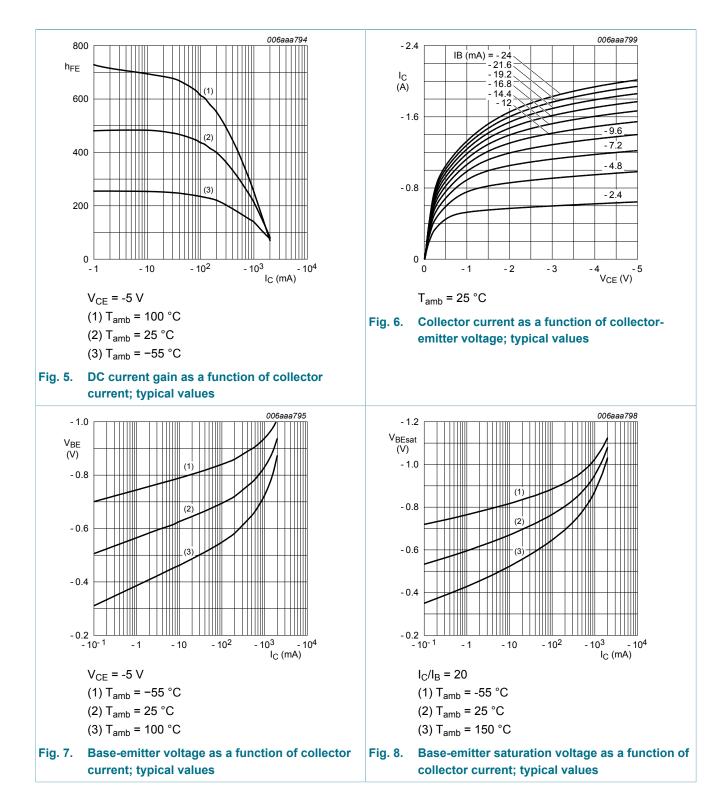
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB}$ = -32 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	$V_{CB}$ = -32 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>CES</sub>	collector-emitter cut-off current	$V_{CE}$ = -32 V; $V_{BE}$ = 0 V; $T_{amb}$ = 25 °C	-	-	-100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -5 V; I <sub>C</sub> = -1 mA; T <sub>amb</sub> = 25 °C	300	-	-	
		$\begin{split} V_{CE} &= -5 \text{ V}; \text{ I}_{C} = -500 \text{ mA};  \text{t}_{p} \leq 300  \mu\text{s}; \\ \bar{\delta} &\leq 0.02;  \text{T}_{amb} = 25 ^{\circ}\text{C} \end{split}$	215	-	-	
		$\begin{split} V_{CE} &= -5 \text{ V}; \text{ I}_{C} = -1 \text{ A};  \text{t}_{p} \leq 300  \mu\text{s}; \\ \bar{\delta} &\leq 0.02;  \text{T}_{amb} = 25 ^{\circ}\text{C} \end{split}$	145	-	-	
		$V_{CE}$ = -5 V; I <sub>C</sub> = -2 A; t <sub>p</sub> ≤ 300 µs; $\delta \le 0.02$ ; T <sub>amb</sub> = 25 °C; pulsed	55	-	-	
V <sub>CEsat</sub>	collector-emitter	$I_{C}$ = -100 mA; $I_{B}$ = -1 mA; $T_{amb}$ = 25 °C	-	-	-140	mV
	saturation voltage	$\begin{split} I_{C} &= -500 \text{ A};  I_{B} = -50 \text{ mA};  t_{p} \leq 300  \mu\text{s}; \\ \delta &\leq 0.02;  T_{amb} = 25 ^{\circ}\text{C} \end{split}$	-	-	-170	mV
		$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-320	mV
		$I_{C}$ = -2 A; $I_{B}$ = -200 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-650	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	320	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = -1 A; $I_{B}$ = -100 mA; pulsed; $t_{p} \le 300$ μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = -5 V; I <sub>C</sub> = -1 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-1.1	V
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = -10 V; I <sub>C</sub> = -50 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	150	-	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	12	pF



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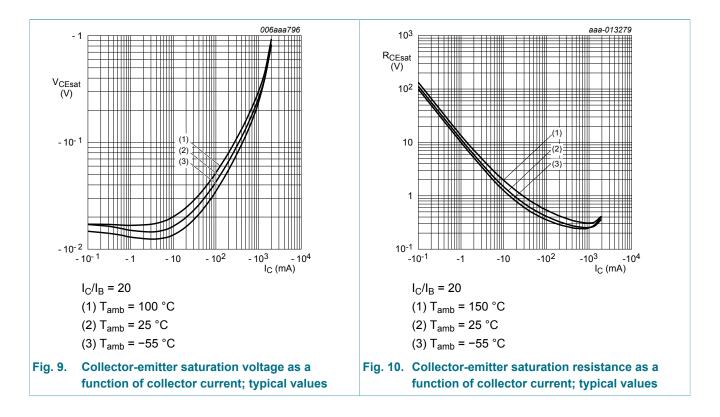
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### **11. Test information**

#### **11.1 Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

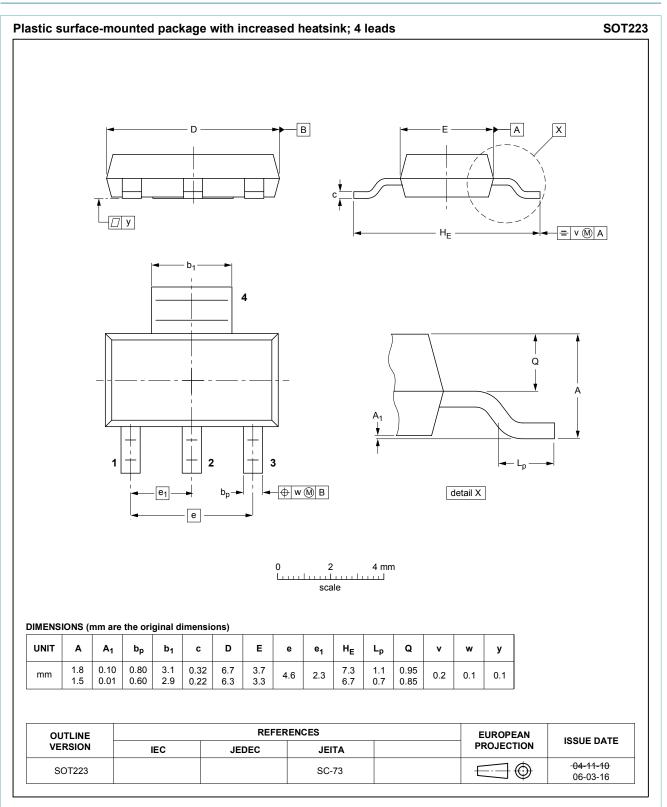
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# 12. Package outline



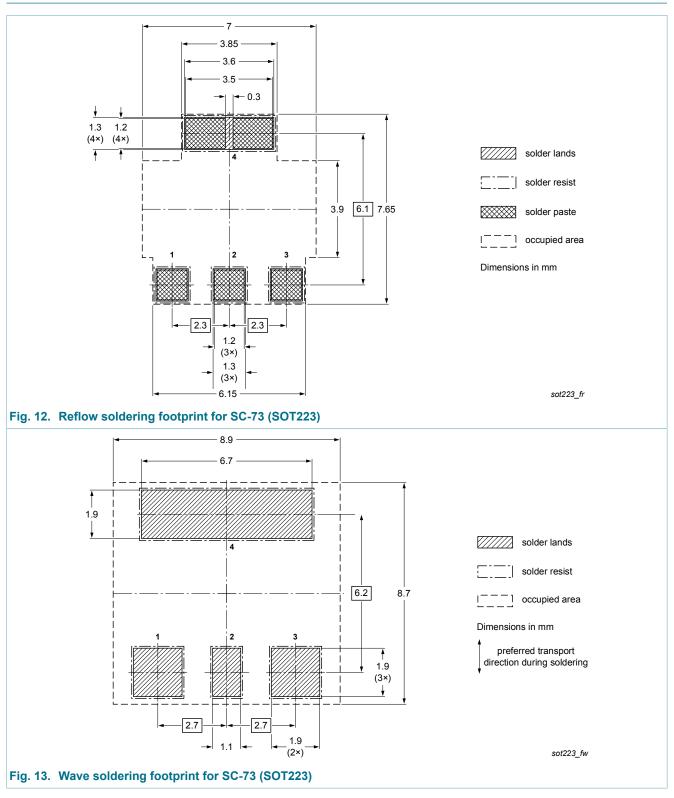
#### Fig. 11. Package outline SC-73 (SOT223)



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## 13. Soldering



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### 14. Revision history

Table 8. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS5240Z v.1	20141015	Product data sheet	-	-			

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#### 40 V, 2 A PNP low VCEsat (BISS) transistor

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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